

# PROCESS FOR FORMING SILICON OXIDE MATERIAL

## ABSTRACT OF THE DISCLOSURE

A thin layer of silicon oxide is formed by cyclic introduction of a silicon-  
5 containing precursor gas and an oxidizing gas separated by an intervening purge step. The  
resulting thin oxide layer enables subsequent conventional CVD of oxide to produce a more  
uniform deposited oxide layer over nonhomogenous surfaces, for example the silicon nitride  
mask/thermal oxide liner surfaces created during fabrication of shallow trench isolation  
structures.

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